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FFP08S60S Stealth 2 Rectifier

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AIRCHILD

SEMICONDUCTOF

FFP08S60S Stealth 2 Rectifier

Features

- + High Speed Switching (Max. $t_{rr}{<}30\text{ns} @ \text{I}_{\text{F}}{=}8\text{A}$)
- High Reverse Voltage and High Reliability
- Avalanche Energy Rated

Applications

- General Purpose
- Switching Mode Power Supply
- Boost Diode in continuous mode power factor corrections
- Power switching circuits

Pin Assignments



8A, 600V Stealth2 Rectifier

The FFP08S60S is stealth 2 rectifier with soft recovery characteristics (t_{rr} <30ns). They has half the recovery time of hyperfast rectifier and are silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as freewheeling of boost diode in switching power supplies and other power swithching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

1 Cathode 2. Anode

Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{RRM}	Peak Repetitive Reverse Voltage	600	V
V _{RWM}	Working Peak Reverse Voltage	600	V
V _R	DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current @ T _C = 115 °C	8	А
IFSM	Non-repetitive Peak Surge Current 60Hz Single Half-Sine Wave	80	A
T _{J,} T _{STG}	Operating Junction and Storage Temperature	- 65 to +150	°C

Thermal Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Max	Units
$R_{ ext{ heta}JC}$	R _{0JC} Maximum Thermal Resistance, Junction to Case		°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
F08S60S	FFP08S60STU	TO-220-2L	-	-	50

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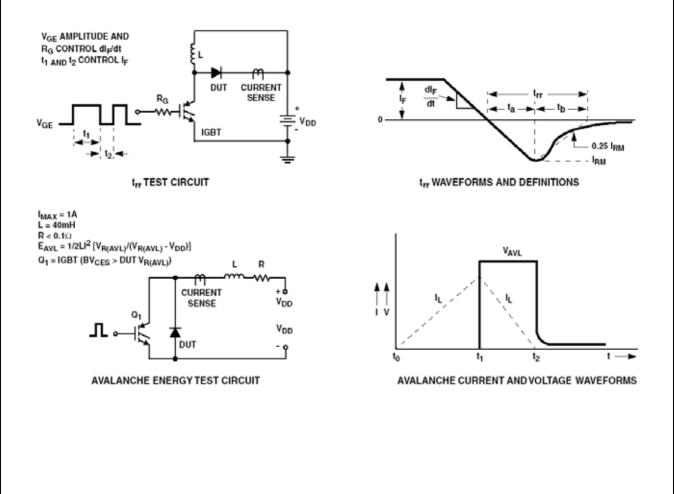
Parameter	Conditions			Тур.	Max	Units
V _{FM} ¹	I _F = 8A I _F = 8A	T _C = 25 °C T _C = 125 °C	-	2.1 1.6	2.6 -	V V
I _{RM} ¹	$V_R = 600V$ $V_R = 600V$	T _C = 25 °C T _C = 125 °C	-	-	100 500	μΑ μΑ
t _{rr}	$I_{F} = 1A, di/dt = 100A/\mu s, V_{R} = 30V$	T _C = 25 °C	-	-	25	ns
trr Irr S factor Q _{rr}	I _F =8A, di/dt = 200A/μs, V _R = 390V	T _C = 25 °C		19 2.2 0.6 21	30 - - -	ns A nC
trr Irr S factor Q _{rr}	I _F =8A, di/dt = 200A/μs, V _R = 390V	T _C = 125 °C		58 4.3 1.3 125		ns A nC
W _{AVL}	Avalanche Energy (L = 40mH)		20	-	-	mJ

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Notes:

1. Pulse : Test Pulse width = 300μ s, Duty Cycle = 2%

Test Circuit and Waveforms



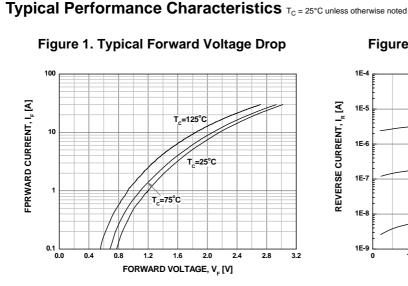


Figure 3. Typical Junction Capacitance

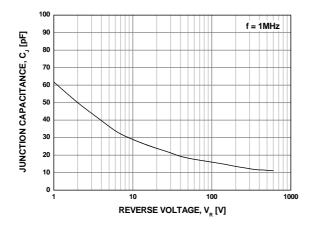


Figure 5. Typical Reverse Recovery Current

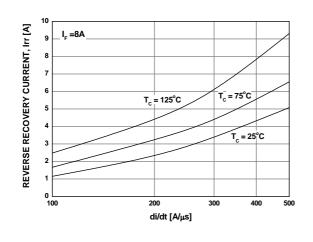


Figure 2. Typical Reverse Current

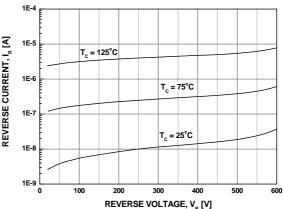


Figure 4. Typical Reverse Recovery Time

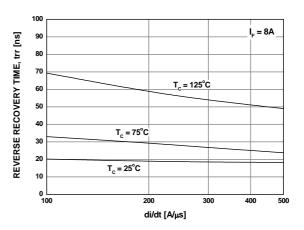
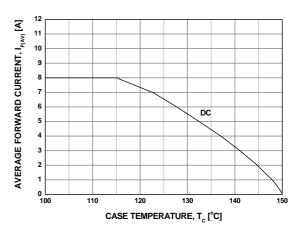
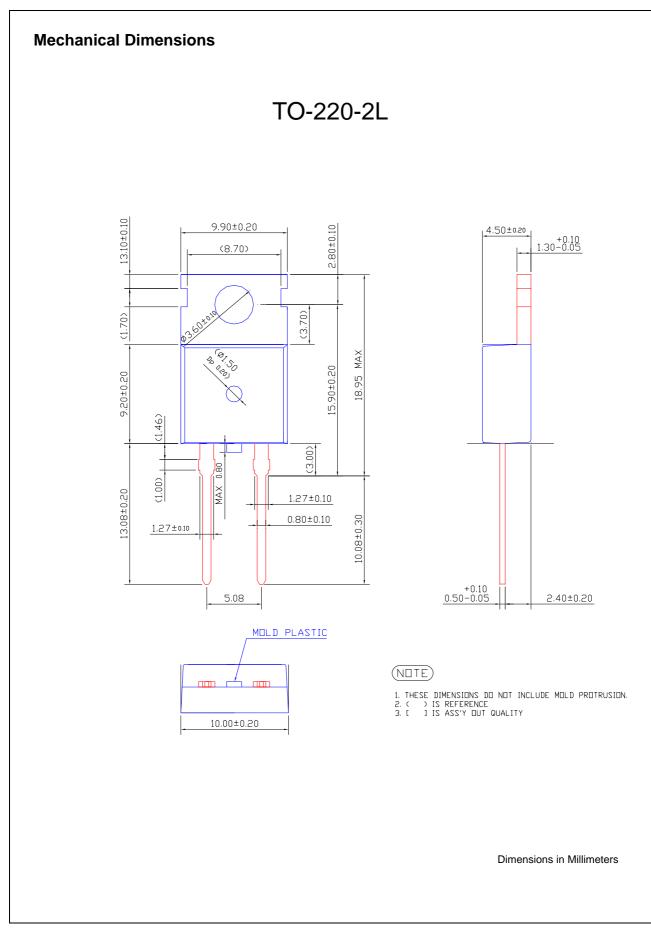


Figure 6. Forward Current Deration Curve







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Build it Now™	ImpliedDisconnect [™]	Programmable Active Droop™	U.
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